

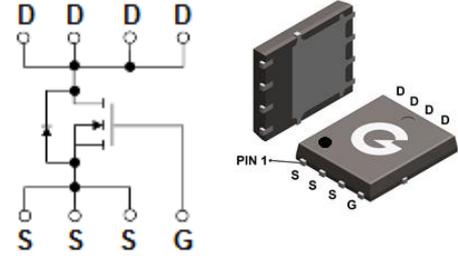
### Features

- Low gate charge minimize switching loss
- Fast recovery body diode

HF

### Mechanical Data

- Case: PDFN5x6-8L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



PDFN5x6-8L

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL021N04T-5DL8	PDFN5x6-8L	5000 pcs / Tape & Reel	021N04T

### Maximum Ratings (@ T<sub>C</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	40	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (T <sub>C</sub> = 25°C, silicon limited)	I <sub>D</sub>	140	A
Continuous Drain Current (T <sub>C</sub> = 25°C, package limited)	I <sub>D</sub>	100	A
Continuous Drain Current (T <sub>C</sub> = 100°C)	I <sub>D</sub>	88	A
Pulsed Drain Current (t <sub>p</sub> =10us, T <sub>A</sub> = 25°C)	I <sub>DM</sub>	320	A
Single Pulse Avalanche Energy <sup>2</sup>	E <sub>AS</sub>	120	mJ

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>D</sub>	62.5	W
Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>D</sub>	3.4	W
Thermal Resistance Junction-to-Air <sup>3</sup>	R <sub>θJA</sub>	37	°C/W
Thermal Resistance Junction-to-Case	R <sub>θJC</sub>	2	°C/W
Operating Junction Temperature Range	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C

### Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32V, V_{GS} = 0V$	-	-	1	$\mu A$
		$V_{DS} = 32V, V_{GS} = 0V, T_J = 85^\circ\text{C}$	-	-	30	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$R_{DS(ON)}$	Static Drain-Source On-resistance	$V_{GS} = 10V, I_D = 20A$	-	1.5	2.1	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	-	2.2	3.0	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	1.9	2.5	V
$R_G$	Gate Resistance	$V_{GS} = 0V, f = 1\text{MHz}$	-	2.6	-	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{ISS}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 20V$ $f = 150\text{KHz}$	-	4878	-	pF
$C_{OSS}$	Output Capacitance		-	1190	-	
$C_{RSS}$	Reverse Transfer Capacitance		-	60	-	
<b>Switching Characteristics</b>						
$t_{d(ON)}$	Turn-on Delay Time	$V_{DS} = 20V$ $V_{GS} = 10V$ $R_G = 0.5\Omega$ $I_D = 20A$	-	12	-	ns
$t_r$	Turn-on Rise Time		-	56	-	
$t_{d(OFF)}$	Turn-Off Delay Time		-	65	-	
$t_f$	Turn-Off Fall Time		-	8.5	-	
$Q_G$	Total Gate-Charge	$V_{DS} = 20V$ $V_{GS} = 4.5V$ $I_D = 10A$	-	34.2	-	nC
$Q_{GS}$	Gate to Source Charge		-	12	-	
$Q_{GD}$	Gate to Drain (Miller) Charge		-	10	-	
<b>Source-Drain Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 20A, V_{GS} = 0V$	-	0.77	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 20A, V_{GS} = 0V$ $di_{SD}/dt = 100A/\mu s$	-	90	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	145	-	nC

Notes:

- Pulse width  $\leq 380\mu s$ ; duty cycle  $\leq 2\%$
- The  $E_{AS}$  data shows Max. rating. The test condition is  $L = 0.5\text{mH}$ ,  $V_{DD} = 20V$ ,  $V_{GS} = 10V$
- The data tested by surface mounted on 1 inch<sup>2</sup> FR-4 board with 2OZ copper

Ratings and Characteristics Curves (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

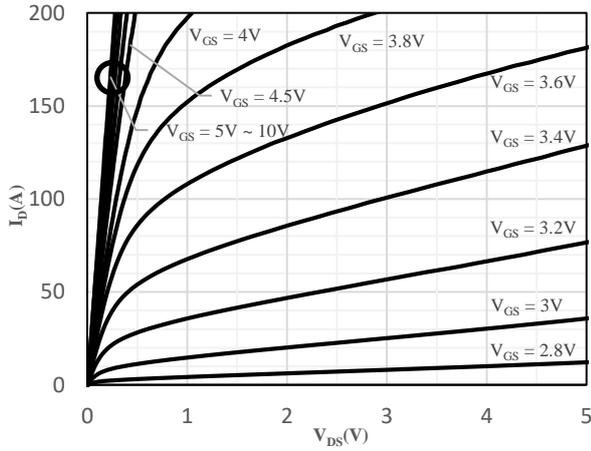


Fig 1 Typical Output Characteristics

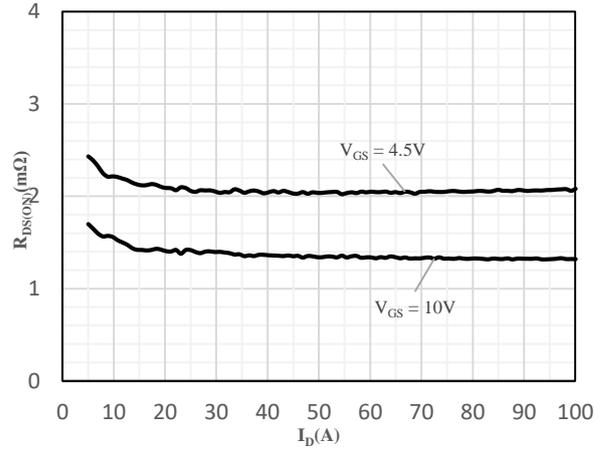


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

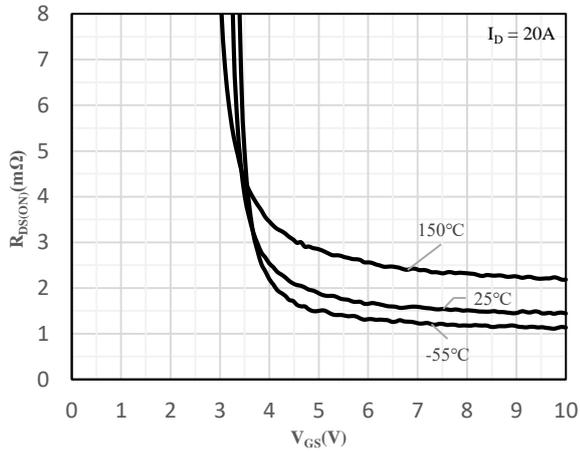


Fig 3 On-Resistance vs. Gate-Source Voltage

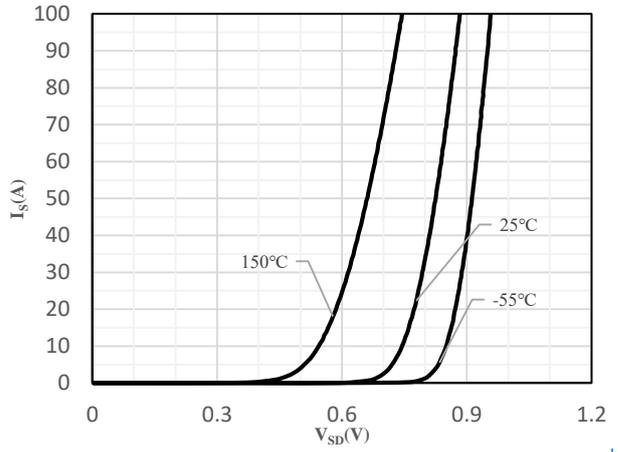


Fig 4 Body-Diode Characteristics

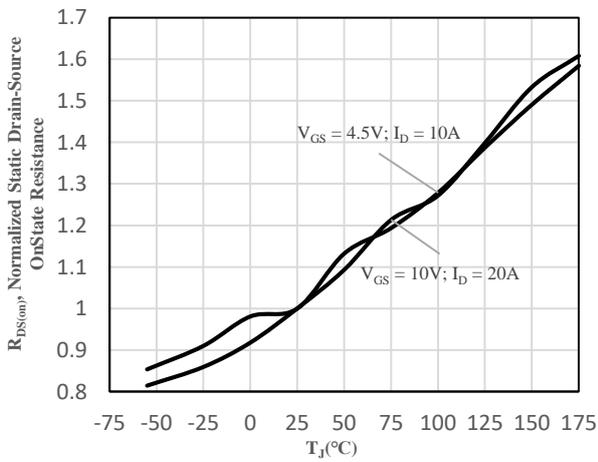


Fig 5 Normalized On-Resistance vs. Junction Temperature

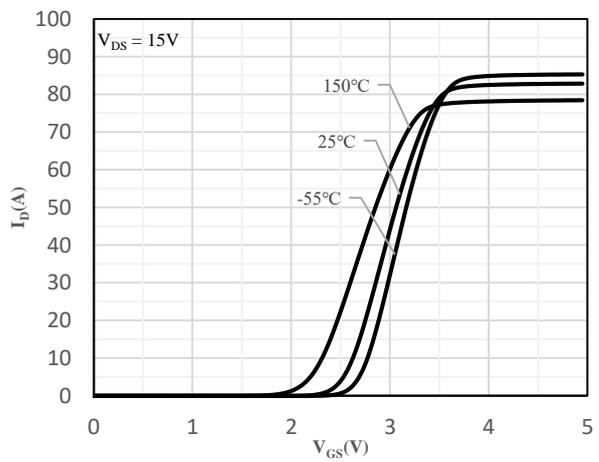


Fig 6 Transfer Characteristics

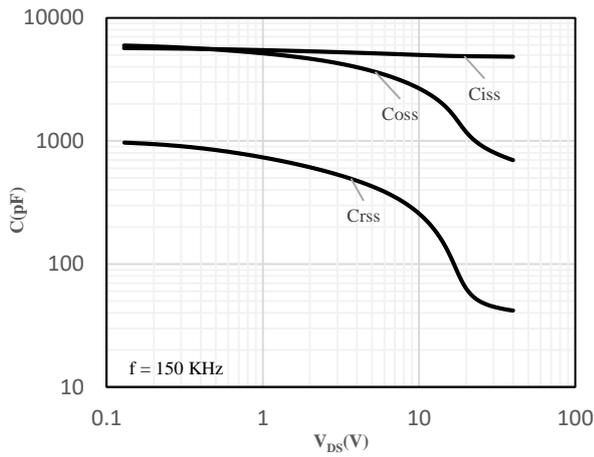


Fig 7 Capacitance Characteristics

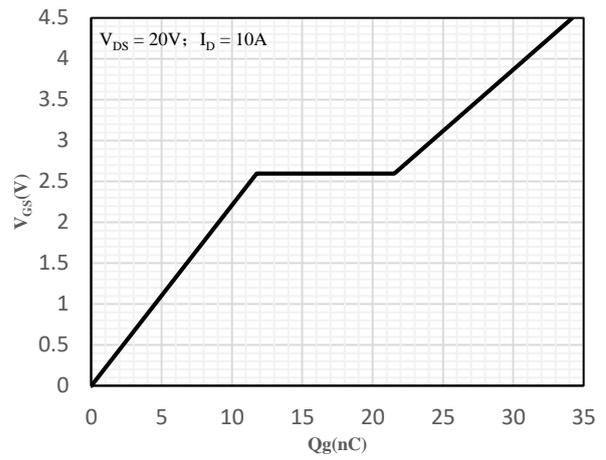


Fig 8 Gate-Charge Characteristics

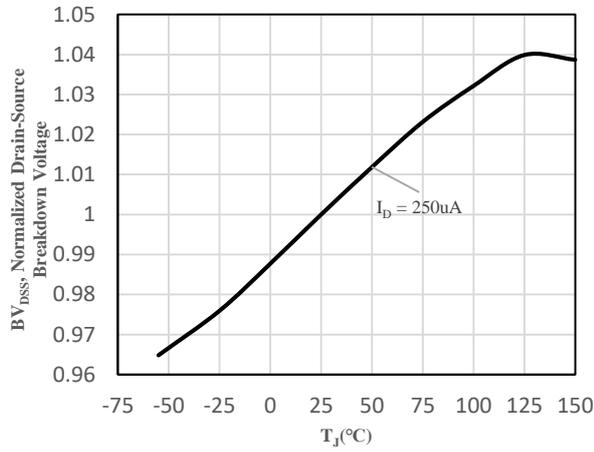


Fig 9 Normalized Breakdown Voltage vs. Junction Temperature

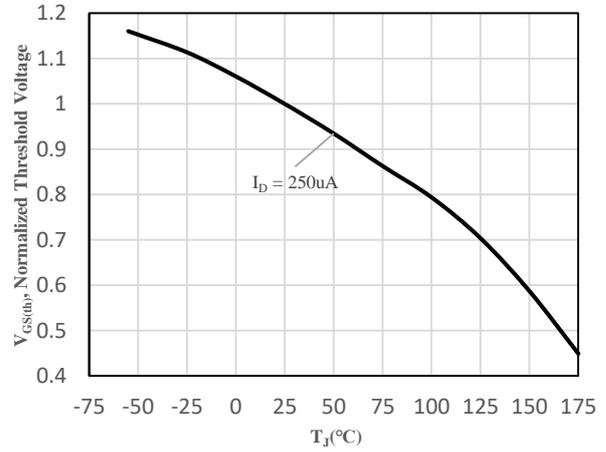


Fig 10  $V_{GS(th)}$  vs. Junction Temperature

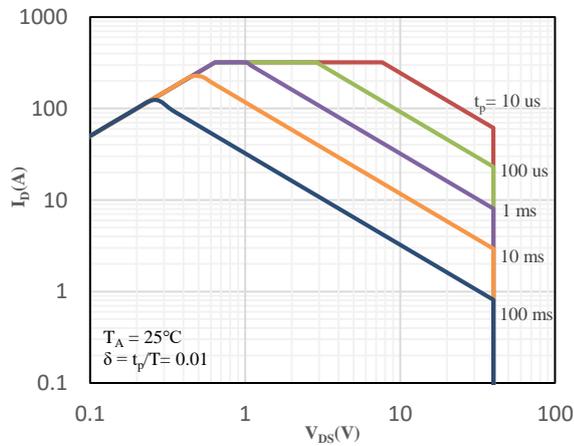


Fig 11 Safe Operation Area

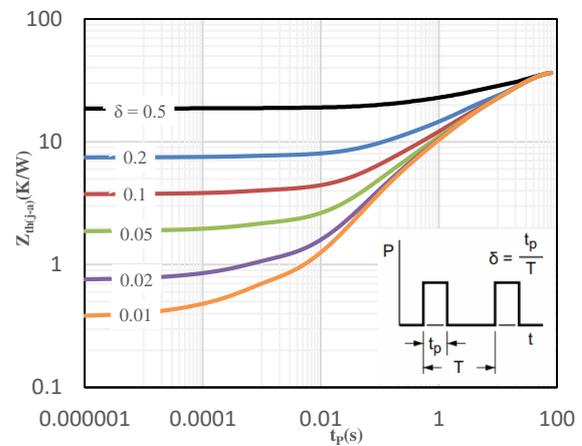
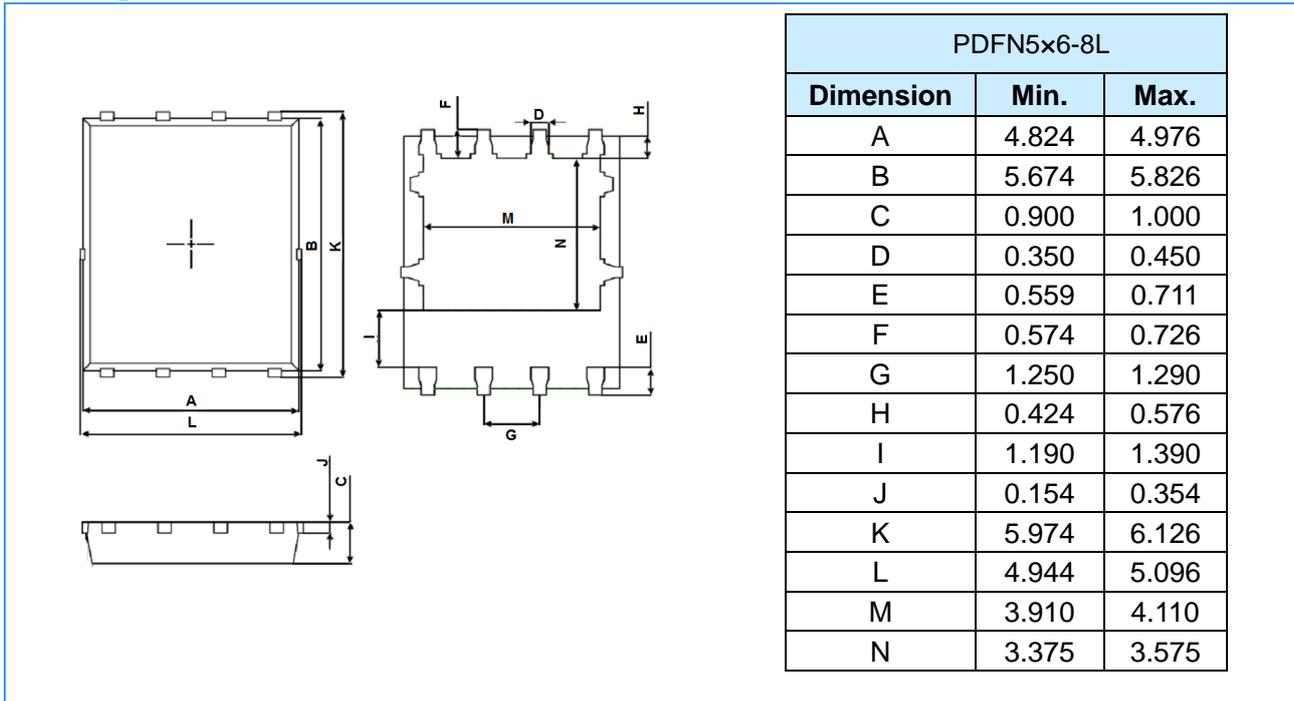
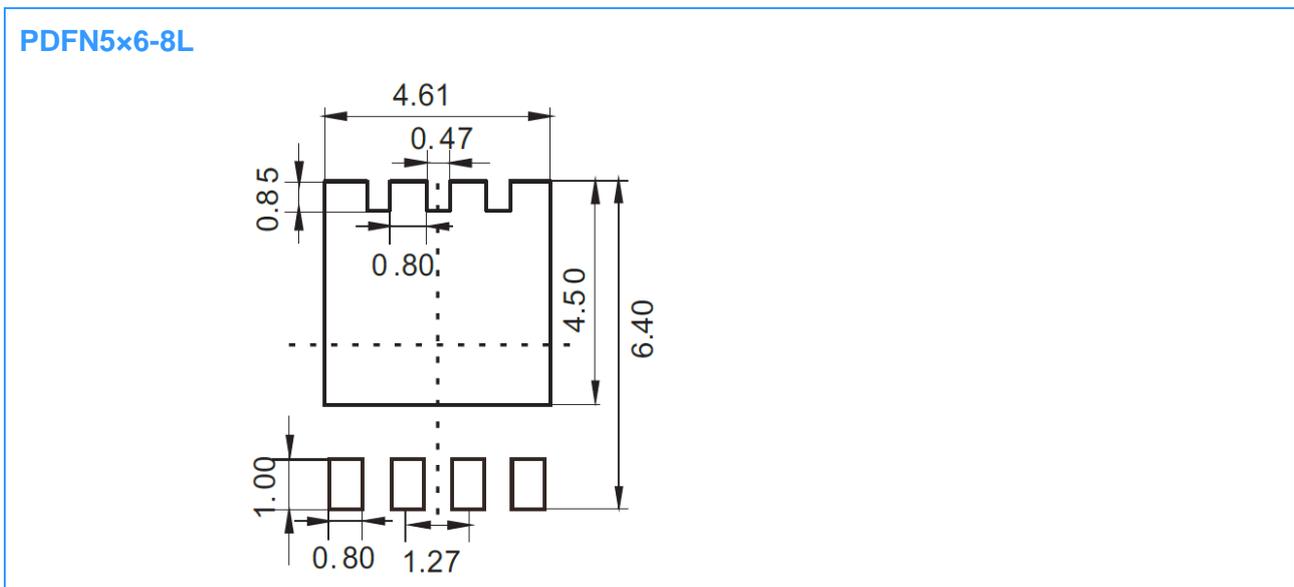


Fig 12 Maximum transient thermal impedance

### Package Outline Dimensions (Unit: mm)



### Mounting Pad Layout (Unit: mm)



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